

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A nitride semiconductor substrate comprising:
a group III nitride semiconductor substrate;
a mask formed over the group III nitride semiconductor substrate; and
a semiconductor multilayer film formed above the mask;
wherein the group III nitride semiconductor substrate has a dislocation density in the vicinity of the surface thereof of $1 \times 10^7/\text{cm}^2$ or less, and
the mask ~~having~~has a polycrystalline material deposited on the surface thereof.
2. (original): The nitride semiconductor substrate according to Claim 1, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.
3. (original): The nitride semiconductor substrate according to Claim 1, wherein voids are formed on the surface of the mask having the polycrystalline material.
4. (original): The nitride semiconductor substrate according to Claim 1, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.
5. (canceled).

6. (currently amended): A nitride semiconductor device comprising:

a group III nitride semiconductor substrate;

a mask formed over the group III nitride semiconductor substrate; and

a semiconductor multilayer film formed above the mask, the semiconductor multilayer film including an active layer;;

wherein the group III nitride semiconductor substrate has a dislocation density in the vicinity of the surface thereof of $1 \times 10^7/\text{cm}^2$ or less, and

the mask has a polycrystalline material deposited on the surface thereof.

7. (original): The nitride semiconductor device according to Claim 6, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.

8. (original): The nitride semiconductor device according to Claim 6, wherein voids are formed on the surface of the mask having the polycrystalline material.

9. (original): The nitride semiconductor device according to Claim 6, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

10. (canceled).

11. (currently amended): The nitride semiconductor device according to Claim 6,
wherein the mask is provided in the vicinity of a device separating plane-groove of the nitride
semiconductor device.

12-21. (canceled).